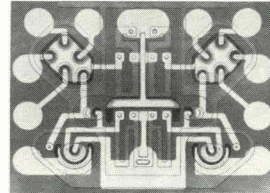


LOAD-COMPENSATED DTL INTEGRATED CIRCUIT

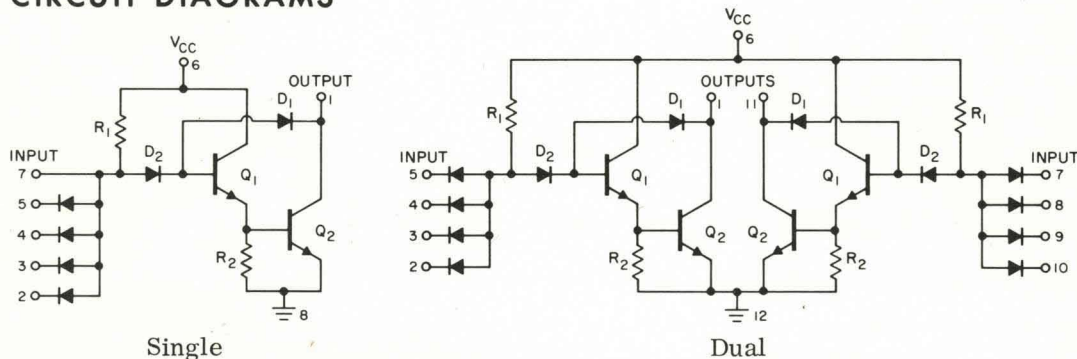
TYPES ZA01A AND ZA02A SINGLE AND DUAL NAND/NOR GATES

ONE OR TWO DIODE-TRANSISTOR LOGIC CIRCUITS IN A SINGLE CHIP OF SILICON

- Low Power-Speed Product - 60 pico-watt-sec
- Operates From Single Power Supply
- Typical Propagation Delay Time - 12 nsec
- Typical Power Dissipation - 5mw
- High Fan-Out-5 at -55 to 70°C



CIRCUIT DIAGRAMS

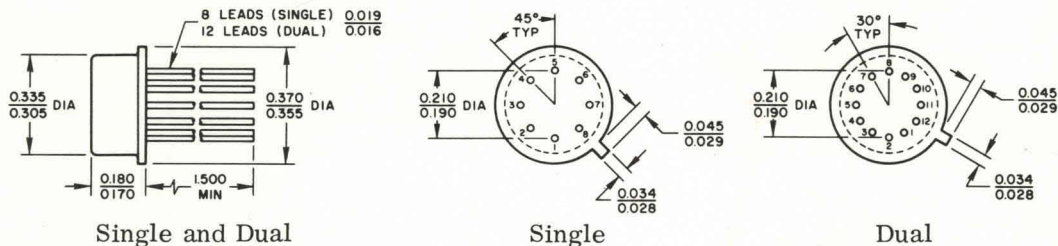


The logic operation of this circuit is identical with conventional DTL. The unique emitter-follower diode-clamp arrangement provides high-speed switching, high gain and low-power operation.

MECHANICAL DATA

Single gate in modified 8-lead TO-5 package
Dual gate in modified 12-lead TO-5 package
(both available in flat package by July 1963)

Pin 8 (single) and pin 12 (dual) are in electrical contact with the case.



All dimensions in inches

PRODUCT CONDITIONING

Long life and mechanical reliability are ensured by subjecting each unit to the following tests:

- High Temperature Storage: 72 hours at 200°C
- Thermal Shock: +200°C to -65°C for 5 Cycles
- 30,000G Centrifuge in the Y₁ Plane
- Helium and Gross Leak Tests for Hermeticity
- Post-Bake Clean-Up to Assure Solderability

Siliconix incorporated

OPERATIONAL CHARACTERISTICS AT $V_{CC}=4v$

Characteristic	Min	Typ	Max	Unit
Fan-in at -55 to +70°C			4 [†]	
Fan-out at $T_A = 70^\circ C, \Delta V = 0.1 v$ (see Note 1)			5	
Worst-Case DC Stability, ΔV , at 70°C Fan-out = 5	100			mv
Power Dissipation per Gate at 25°C (see Note 2)		5		mw
Average Propagation Delay per Gate (see pp. 3,4), When Fan-in = 1 and Fan-out = 1, at $T_A = +25^\circ C$ $T_A = -55^\circ C$ $T_A = 70^\circ C$		12 14 14	15	nsec nsec nsec

† Diode array available for single gate to improve fan-in.

ABSOLUTE MAXIMUM RATINGS AT 25° C

Power Supply Voltage, V_{CC}	6 v
Gate Input Voltage	6 v
Gate Output Voltage (Input Grounded)	6 v
Operating Temperature Range	-55 to +70°C
Storage Temperature Range	-55 to +200°C

STATIC CHARACTERISTICS (WORST-CASE) $V_{CC}=4v$

(See opposite page for test conditions)

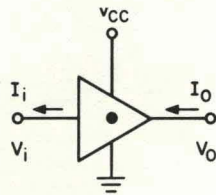
Characteristic	Temperature			Unit
	-55°C	+25°C	+70°C	
I_{OFF} Maximum Output Current with Gate OFF	5*	10*	20*	μa
$I_{R(max)}$ Maximum Reverse Current per Input Diode	0.05*	0.10*	0.30*	μa
$I_{i(max)}$ Maximum Input Current with Gate OFF (Max Load Presented to Driv- ing Stage), with $V_i = V_F - 100 mv$	1.15*	1.30*	1.35*	ma
V_F Maximum Voltage at any Input that will Ensure Turn-OFF (Max False Voltage)	1.38*	1.14*	0.95*	v
$V_{o(max)}$ Maximum Output Voltage When Fully Loaded at: Fan-out = 5 Fan-out = 25	1.02 1.30*	0.94*	0.85*	v v
V_T Minimum Input Voltage that will Ensure Turn-ON (Minimum True Voltage) Fan-out = 5	2.00	1.78	1.62	v
ΔV DC Stability Margin ($V_F - V_o$) Fan-out = 5	0.36*	0.20*	0.10*	v

*Characteristics so designated are tested on every unit

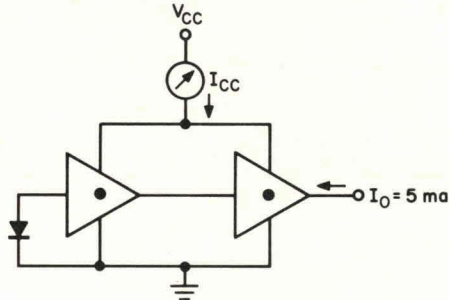
Notes:

1. This is the maximum fan-out permissible for worst-case logic design with a 4 v power supply when the d-c stability ΔV margin is 0.1 v.
2. Power dissipation is defined as power supply voltage times average current drawn per gate. (See test circuit, p. 3).

MEASUREMENT OF STATIC CHARACTERISTICS



General Test Circuit



Power Dissipation Test Circuit

$$\text{Power dissipation per gate} = \frac{V_{CC} \times I_{CC}}{2}$$

As measured above, the power dissipation is the average between the OFF stage and typically loaded ON stage and is equivalent to a 50% duty cycle for a single gate.

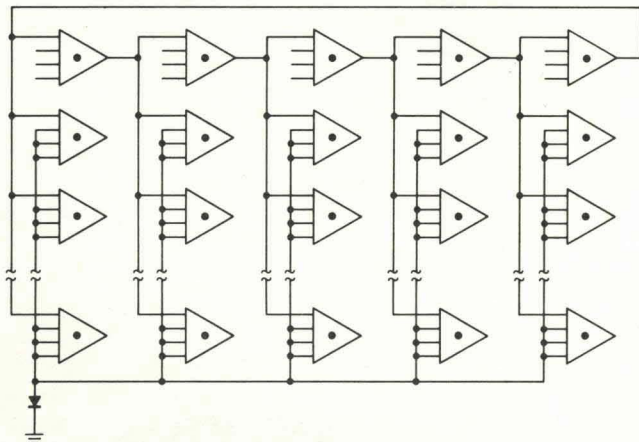
TEST CONDITIONS

Characteristic to be Determined	Set or Measure These Characteristics - e.g., to Determine V_F at 25°C, Set I_o at 10 μ a, V_o at 4 v, Measure V_i .				Other Conditions
	I_i Input Current	V_i Input Voltage	I_o Output Current	V_o Output Voltage	
V_F		Measure	I_{OFF}^*	4 v	Free inputs connected to V_{CC}
$I_{i(max)}$	Measure	$V_F^* - 100$ mv		4 v	Free inputs connected to V_{CC}
$I_{R(max)}$	Measure	4 v			Open circuit output One input grounded
$V_{o(max)}$	F.I. $[I_{OFF}^* + (F.O. - 1) I_{R(max)}]^*$		F.O. $\times I_{i(max)}^*$	Measure	
V_T	$I_{OFF}^* + (F.O. - 1) I_{R(max)}^*$		Measure	F.O. $\times I_{i(max)}^*$	Free inputs open

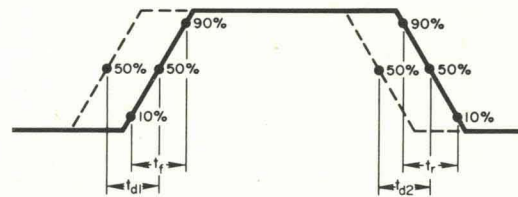
F.I. = fan-in F.O. = fan-out

* Definitions and values for temperatures from -55 to +70°C obtained from table on opposite page.

MEASUREMENT OF DYNAMIC CHARACTERISTICS



Test Circuit for Propagation Delay/Fan-out Measurements



t_d = PROPAGATION DELAY
 t_r = RISE TIME
 t_f = FALL TIME

Waveform propagated through two stages.
 Average propagation delay per stage

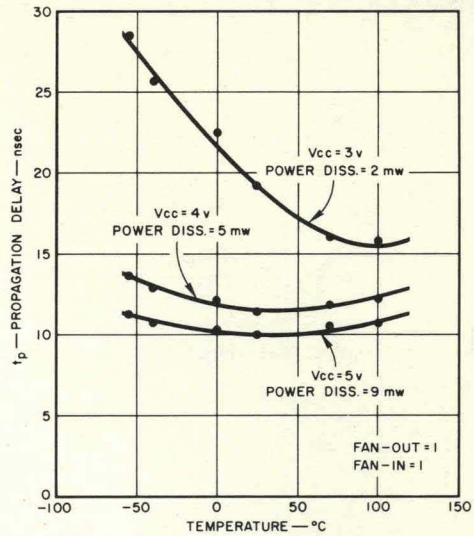
$$t_{d(avg)} = \frac{t_{d1} + t_{d2}}{4}$$

Waveforms and Time Delays

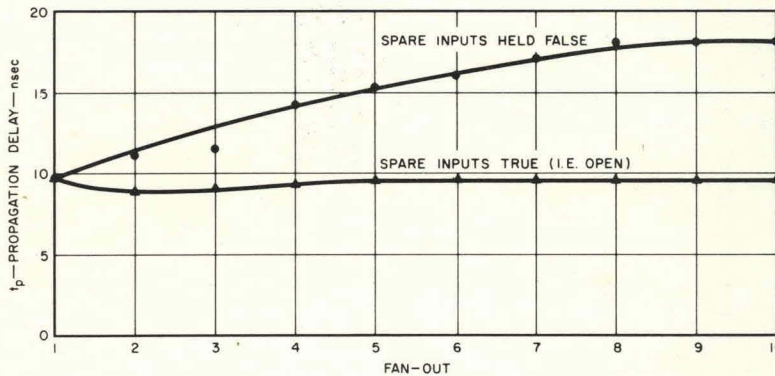
DYNAMIC CHARACTERISTICS

TIME	FAN-OUT		UNIT	
	1	10 (FREE INPUTS OPEN)		10 (FREE INPUTS HELD FALSE)
t_r 0-1 (TRANSIENT)	10	18	30	nsec
t_f 1-0 (TRANSIENT)	5	20	20	nsec

Typical Rise and Fall Times
 $V_{CC} = 4 \text{ volts, } +25^\circ\text{C}$



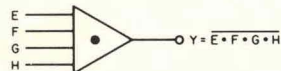
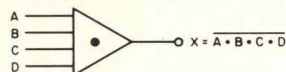
Typical Propagation Delay vs. Voltage and Temp



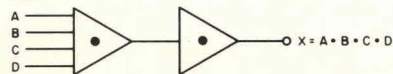
Effect of Loading on Propagation Delay

LOGIC DIAGRAMS

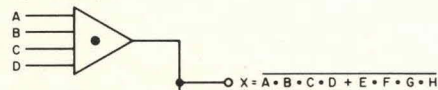
NAND (POSITIVE LOGIC)



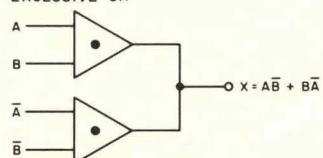
AND



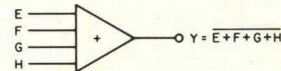
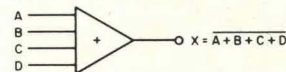
NOT AND-OR



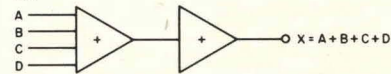
EXCLUSIVE OR



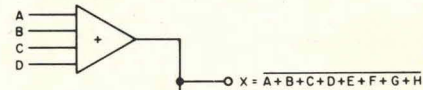
NOR (NEGATIVE LOGIC)



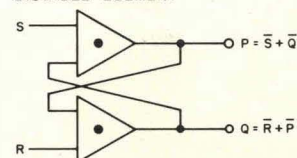
OR



8 INPUT NOR



BISTABLE ELEMENT



Printed in USA
 May 1, 1963